TOSHIBA FIELD EFFECT TRANSISTOR SILICON N CHANNEL MOS TYPE (π-MOSV)

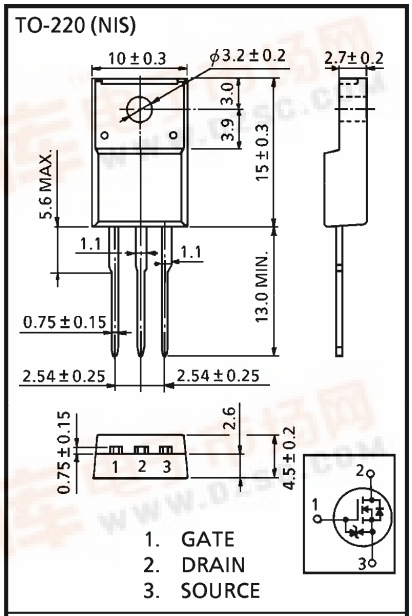
2SK3316

HIGH SPEED, HIGH VOLTAGE SWITCHING APPLICATIONS
SWITCHING REGULATOR APPLICATIONS

INDUSTRIAL APPLICATIONS

Unit in mm

- Fast Reverse Recovery Time : t_{rr} = 60 ns (Typ.)
- Built-in High-Speed Free-Wheeling Diode
- Low Drain-Source ON Resistance : $R_{DS\,(ON)}$ = 1.6 Ω (Typ.)
- High Forward Transfer Admittance : $|Y_{fs}|$ = 3.8 S (Typ.)
- Low Leakage Current : I_{DSS} = 100 μA (Max.) (V_{DS} = 500 V)
- Enhancement-Mode : V_{th} = 2.0~4.0 V (V_{DS} = 10 V, I_D = 1 mA)



JEDEC	—
EIAJ	SC-67
TOSHIBA	2-10R1B

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Drain-Source Voltage		V_{DSS}	500	V
Drain-Gate Voltage (R_{GS} = 20 kΩ)		V_{DGR}	500	V
Gate-Source Voltage		V_{GSS}	±30	V
Drain Current	DC	I_D	5	A
	Pulse	I_{DP}	20	A
Drain Power Dissipation (Tc = 25°C)		P_D	35	W
Single Pulse Avalanche Energy**		E_{AS}	180	mJ
Avalanche Current		I_{AR}	5	A
Repetitive Avalanche Energy*		E_{AR}	3.5	mJ
Channel Temperature		T_{ch}	150	°C
Storage Temperature Range		T_{stg}	−55~150	°C

THERMAL CHARACTERISTICS

CHARACTERISTIC	SYMBOL	MAX.	UNIT
Thermal Resistance, Channel to Case	$R_{th\,(ch\text{-}c)}$	3.57	°C / W
Thermal Resistance, Channel to Ambient	$R_{th\,(ch\text{-}a)}$	62.5	°C / W

Note ;
* Repetitive rating ; Pulse Width Limited by Max. junction temperature.
** V_{DD} = 90 V, T_{ch} = 25°C (initial), L = 12.2 mH, R_G = 25 Ω, I_{AR} = 5 A

This transistor is an electrostatic sensitive device.
Please handle with caution.

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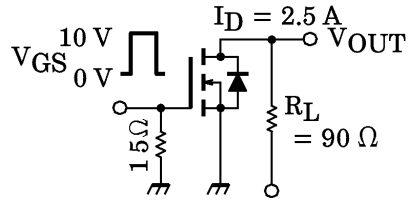
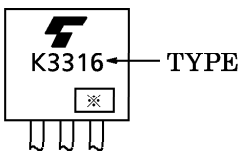
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate Leakage Current		I_{GSS}	V_{GS} = ±25 V, V_{DS} = 0 V	—	—	±10	μA
Gate-Source Breakdown Voltage		$V_{(BR)\,GSS}$	I_G = ±100 μA, V_{DS} = 0 V	±30	—	—	V
Drain Cut-off Current		I_{DSS}	V_{DS} = 500 V, V_{GS} = 0 V	—	—	100	μA
Drain-Source Breakdown Voltage		$V_{(BR)\,DSS}$	I_D = 10 mA, V_{GS} = 0 V	500	—	—	V
Gate Threshold Voltage		V_{th}	V_{DS} = 10 V, I_D = 1 mA	2.0	—	4.0	V
Drain-Source ON Resistance		$R_{DS\,(ON)}$	V_{GS} = 10 V, I_D = 2.5 A	—	1.6	1.8	Ω
Forward Transfer Admittance		$\|Y_{fs}\|$	V_{DS} = 10 V, I_D = 2.5 A	2.5	3.8	—	S
Input Capacitance		C_{iss}	V_{DS} = 10 V, V_{GS} = 0 V, f = 1 MHz	—	780	—	pF
Reverse Transfer Capacitance		C_{rss}		—	60	—	
Output Capacitance		C_{oss}		—	200	—	
Switching Time	Rise Time	t_r	 V_{IN} : t_r, t_f < 5 ns, Duty ≦ 1%, t_w = 10 μs	—	12	—	ns
	Turn-on Time	t_{on}		—	25	—	
	Fall Time	t_f		—	15	—	
	Turn-off Time	t_{off}		—	60	—	
Total Gate Charge (Gate-Source Plus Gate-Drain)		Q_g	V_{DD} ≒ 400 V, V_{GS} = 10 V, I_D = 5 A	—	17	—	nC
Gate-Source Charge		Q_{gs}		—	11	—	
Gate-Drain ("Miller") Charge		Q_{gd}		—	6	—	

SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Continuous Drain Reverse Current	I_{DR}	—	—	—	5	A
Pulse Drain Reverse Current	I_{DRP}	—	—	—	20	A
Diode Forward Voltage	V_{DSF}	I_{DR} = 5 A, V_{GS} = 0 V	—	—	−1.7	V
Reverse Recovery Time	t_{rr}	I_{DR} = 5 A, V_{GS} = 0 V	—	60	—	ns
Reverse Recovery Charge	Q_{rr}	dI_{DR}/dt = 100 A/μs	—	0.1	—	μC

MARKING



※ Lot Number

□□ — Month (Starting from Alphabet A)

Year (Last Number of the Christian Era)